



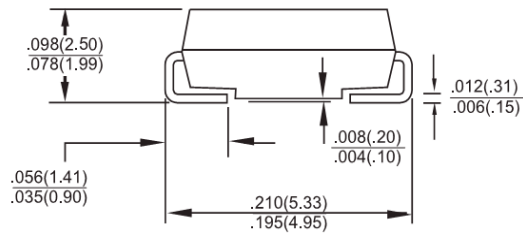
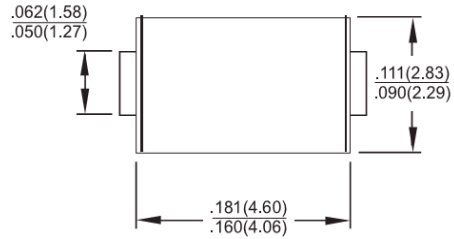
US1A - US1M

1.0AMP. High Efficient Surface Mount Rectifiers

SMA/DO-214AC

Features

- ✧ Glass passivated chip junction
- ✧ For surface mounted application
- ✧ Low profile package
- ✧ Built-in strain relief
- ✧ Ideal for automated placement
- ✧ Easy pick and place
- ✧ Ultrafast recovery time for high efficiency
- ✧ Low forward voltage, low power loss
- ✧ High temperature soldering guaranteed: 260°C/10 seconds on terminals
- ✧ Plastic material used carries Underwriters Laboratory Classification 94V-0
- ✧ Green compound with suffix "G" on packing code & prefix "G" on datecode



Dimensions in inches and (millimeters)

Mechanical Data

- ✧ Case: Molded plastic
- ✧ Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
- ✧ Polarity: Indicated by cathode band
- ✧ Weight: 0.064 grams

Marking Diagram



- US1X = Specific Device Code
- G = Green Compound
- Y = Year
- WW = Work Week

Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	US1A	US1B	US1D	US1G	US1J	US1K	US1M	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	1							A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	30							A
Maximum Instantaneous Forward Voltage (Note 1) @ 1 A	V_F	1.0			1.7			V	
Maximum Reverse Current @ Rated VR $T_A=25\text{ }^\circ\text{C}$ $T_A=125\text{ }^\circ\text{C}$	I_R	5			150			μA	
Maximum Reverse Recovery Time (Note 2)	T_{rr}	50			75			nS	
Typical Junction Capacitance (Note 3)	C_j	15			10			pF	
Typical Thermal Resistance	$R_{\theta JA}$ $R_{\theta JL}$	75			27			$^\circ\text{C/W}$	
Operating Temperature Range	T_J	- 55 to + 150							$^\circ\text{C}$
Storage Temperature Range	T_{STG}	- 55 to + 150							$^\circ\text{C}$

Note 1: Pulse Test with PW=300 usec, 1% Duty Cycle

Note 2: Reverse Recovery Test Conditions: $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $IRR=0.25\text{A}$

Note 3: Measured at 1 MHz and Applied Reverse Voltage of 4.0V D.C.

RATINGS AND CHARACTERISTIC CURVES (US1A THRU US1M)

FIG.1 MAXIMUM FORWARD CURRENT DERATING CURVE

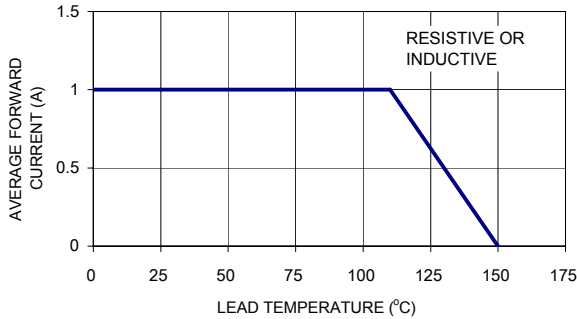


FIG. 2 MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

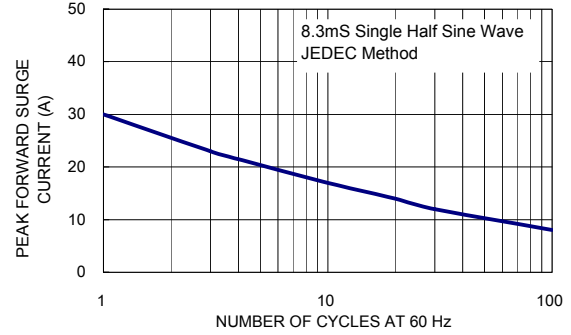


FIG. 3 TYPICAL FORWARD CHARACTERISTICS

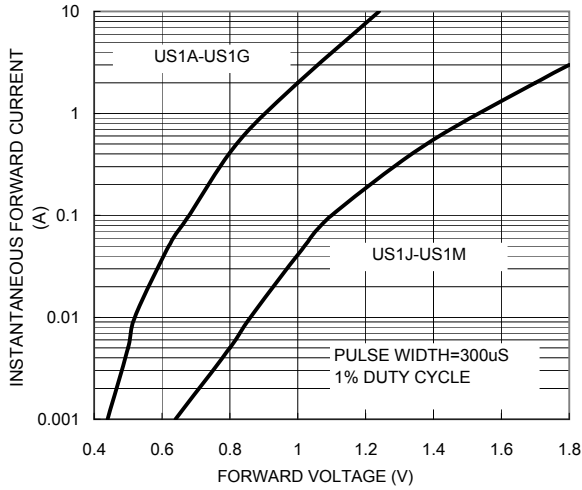


FIG. 4 TYPICAL REVERSE CHARACTERISTICS

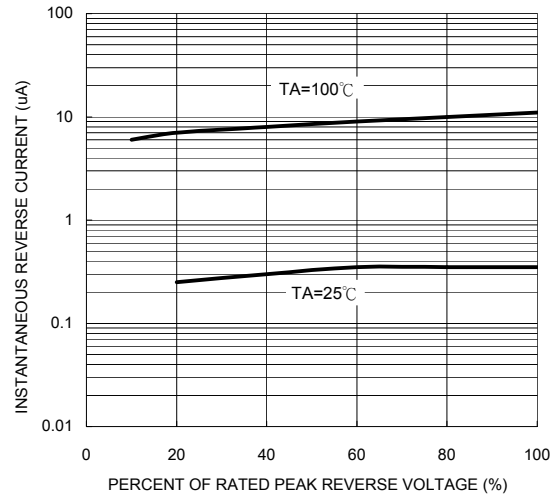


FIG. 5 TYPICAL JUNCTION CAPACITANCE

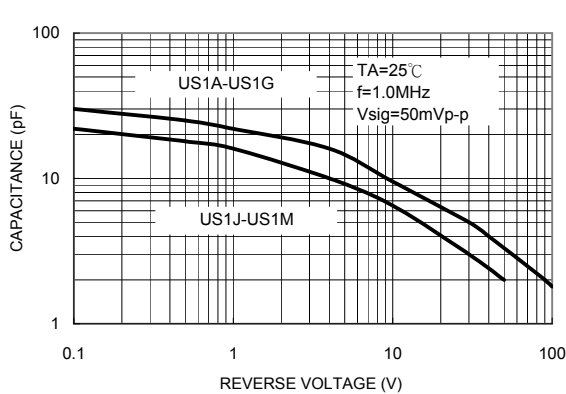


FIG. 6 TYPICAL TRANSIENT THERMAL IMPEDANCE

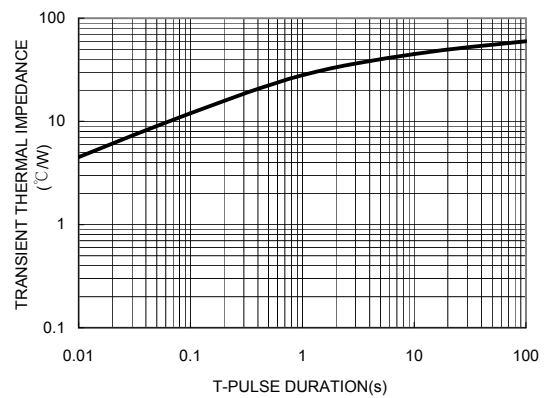
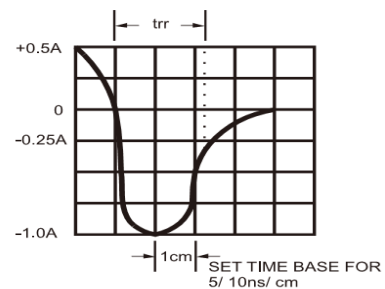
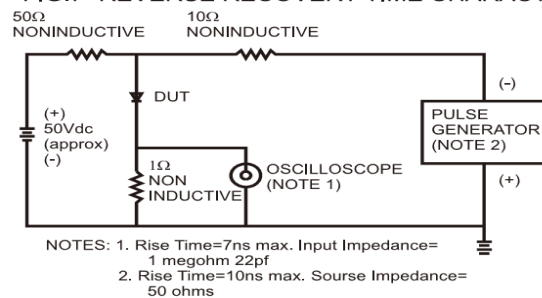


FIG.7- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM



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